

EFFECT OF ULTRASOUND IRRADIATION
ON AN n -CdS/ p -CdTe HETEROSTRUCTURE

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S u m m a r y

The results of photoelectric researches of an intermediate CdTe_{1-x}S_x layer at the interface of the n -CdS/ p -CdTe heterostructure, fabricated by depositing CdS in vacuum onto the CdTe surface, are reported. It has been shown that if the substrate temperature falls within the interval $T_s = 220 \div 240$ °C, besides the stable CdTe_{1-x}S_x compounds, the metastable ones are also formed. The latter disappear after the specimens are subjected to the ultrasound treatment with an irradiation power of 1 W/cm² for 10 min. For the CdTe_{1-x}S_x interlayer, the content x and the crystal lattice constant $a_0(x)$ of the compounds included are calculated on the basis of the photoconductivity spectra for the n -CdS/ p -CdTe heterointerface.